

2SC2612

Silicon NPN Triple Diffused

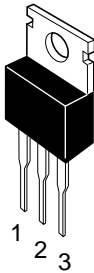
HITACHI

Application

High voltage, high speed and high power switching

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

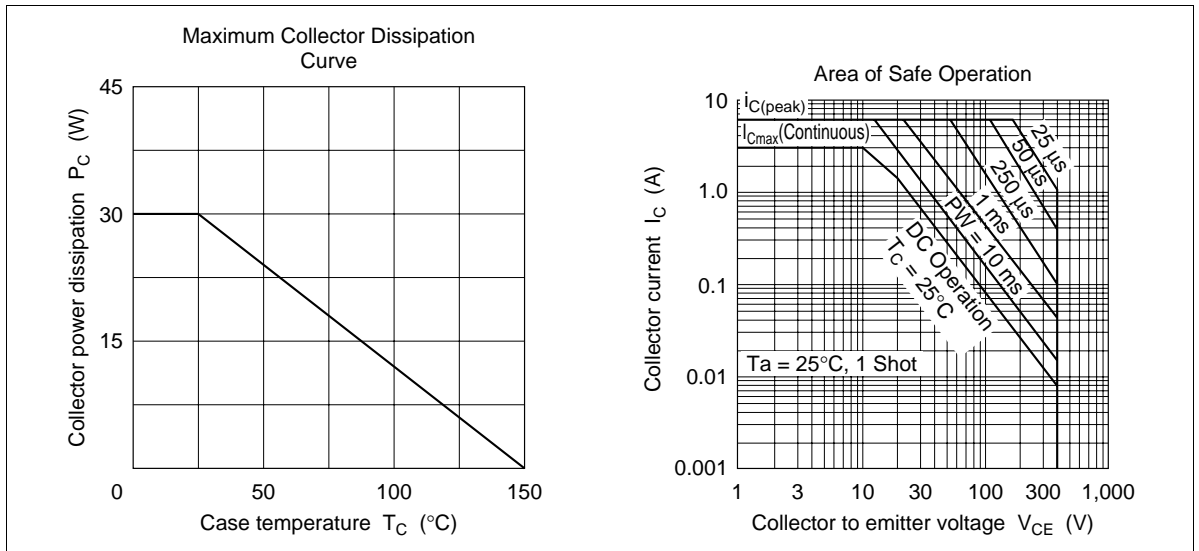
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	3	A
Collector peak current	$I_{C(peak)}$	6	A
Base current	I_B	1.5	A
Collector power dissipation	P_C^{*1}	30	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

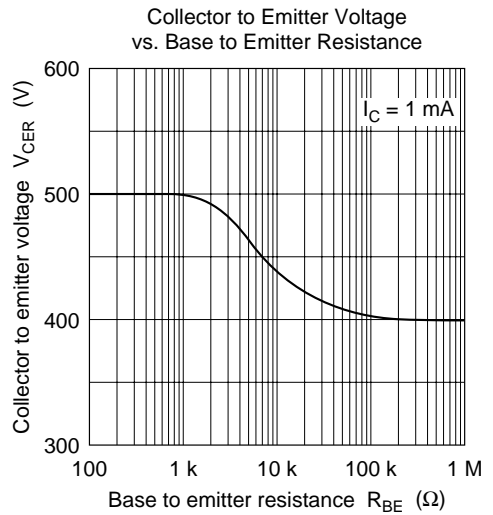
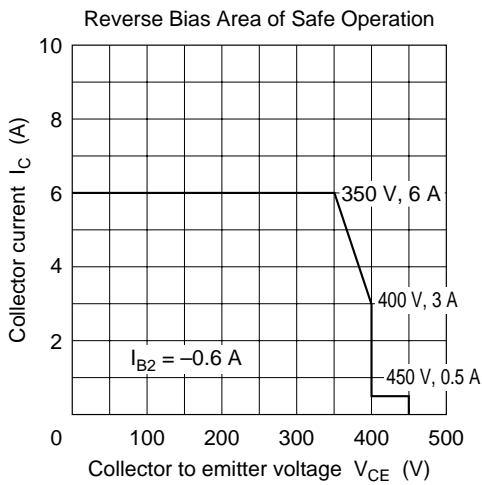
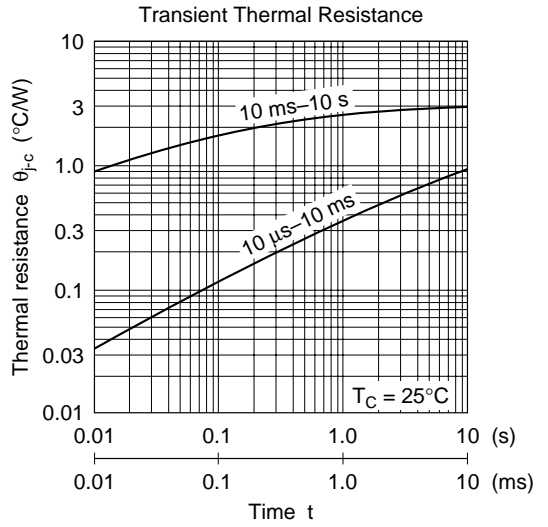
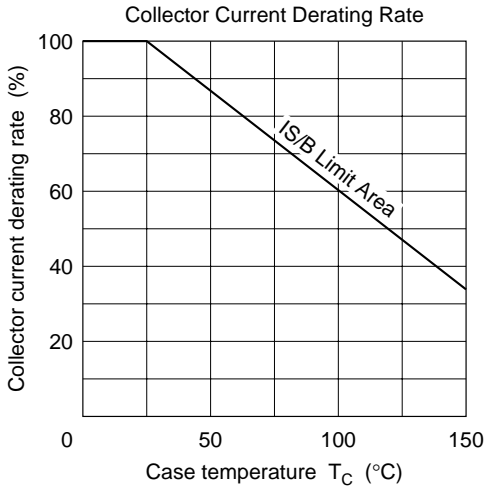
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

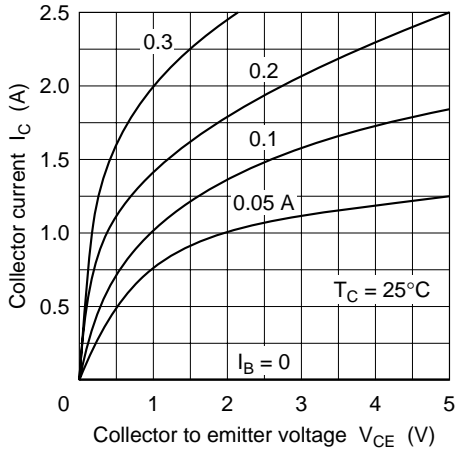
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter sustain voltage	$V_{CEO(sus)}$	400	—	—	V	$I_C = 0.2 \text{ A}$, $R_{BE} = \infty$, $L = 100 \text{ mH}$
	$V_{CEX(sus)}$	400	—	—	V	$I_C = 3 \text{ A}$, $I_{B1} = -I_{B2} = 0.6 \text{ A}$ $V_{BE} = -5 \text{ V}$, $L = 180 \mu\text{H}$, Clamped
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 10 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 400 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	100	μA	$V_{CE} = 350 \text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE1}	15	—	—		$V_{CE} = 5 \text{ V}$, $I_C = 1.5 \text{ A}^{*1}$
	h_{FE2}	7	—	—		$V_{CE} = 5 \text{ V}$, $I_C = 3.0 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 1.5 \text{ A}$, $I_B = 0.3 \text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 1.5 \text{ A}$, $I_B = 0.3 \text{ A}^{*1}$
Turn on time	t_{on}	—	—	1.0	μs	$I_C = 3 \text{ A}$, $I_{B1} = -I_{B2} = 0.6 \text{ A}$,
Storage time	t_{stg}	—	1.2	2.5	μs	$V_{CC} \cong 150 \text{ V}$
Fall time	t_f	—	—	1.0	μs	

Note: 1. Pulse test

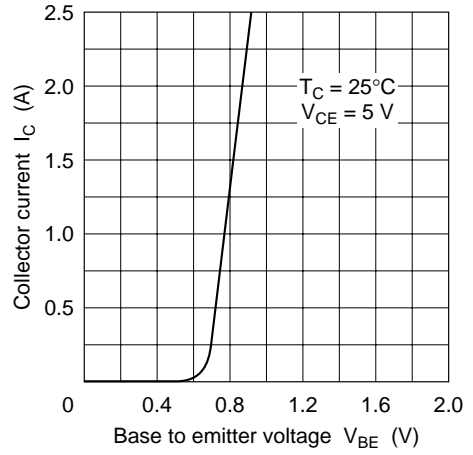




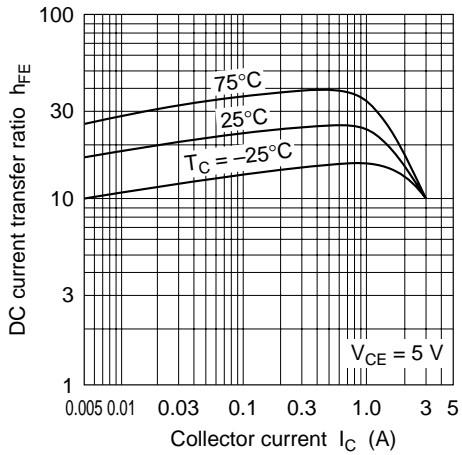
Typical Output Characteristics



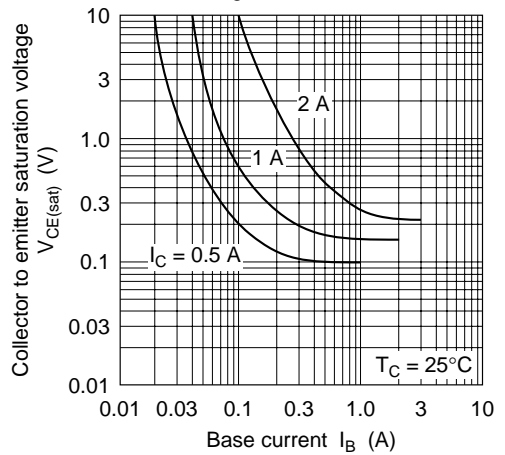
Typical Transfer Characteristics

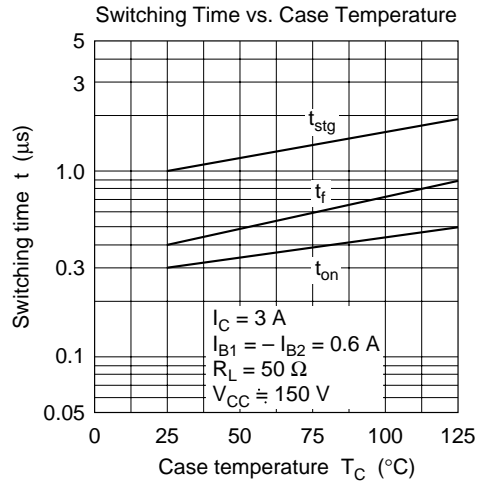
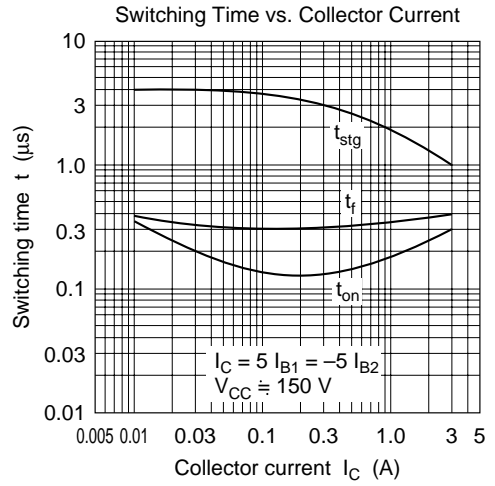
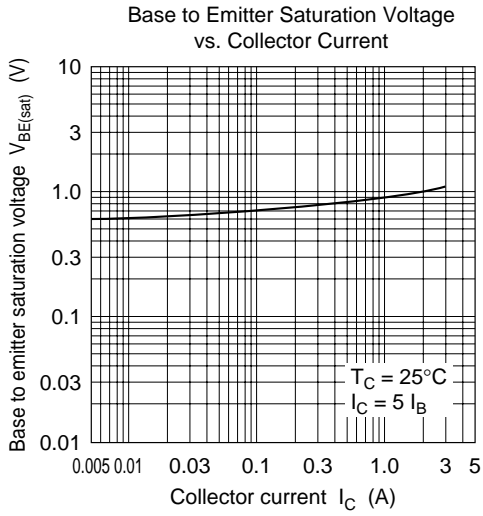


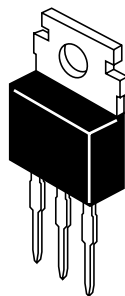
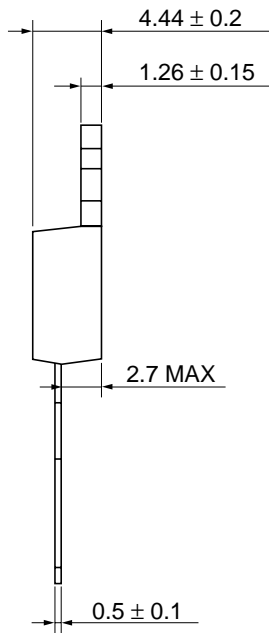
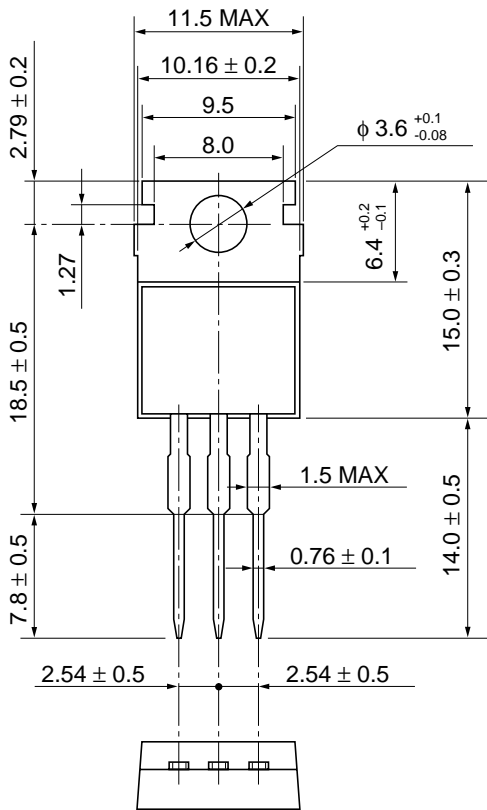
DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Base Current







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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